

TRANSISTOR (PNP)

FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

MAXIMUM RATINGS (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Value	Units	
V _{CBO}	Collector-Base Voltage			
	BC856	-80	V	
	BC857	-50	V	
	BC858	-30		
V _{CEO}	Collector-Emitter Voltage		٧	
	BC856	-65		
	BC857	-45		
	BC858	-30		
V _{EBO}	Emitter-Base Voltage	-5	V	
Ic	Collector Current –Continuous	-0.1	Α	
Pc	Collector Power Dissipation	200	mW	
TJ	Junction Temperature	150	℃	
T _{stg}	Storage Temperature	-65-150	℃	

DEVICE MARKING

BC856A=3A; BC856B=3B;

BC857A=3E;BC857B=3F;BC857C=3G; BC858A=3J; BC858B=3K; BC858C=3L

SOT-23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



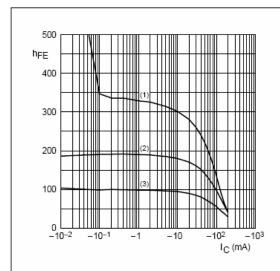
ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage BC856				-80		
BC857		V_{CBO}	I _C = -10μΑ, I _E =0	-50		V
	BC858			-30		
Collector-emitter breakdown voltage BC856				-65		
	BC857	$V_{\sf CEO}$	I_C = -10mA, I_B =0	-45		V
	BC858			-30		
Emitter-base breakdown voltage		V_{EBO}	I _E = -1μΑ, I _C =0	-5		V
Collector cut-off current	BC856		V _{CB} = -70 V , I _E =0			
	BC857	I _{CBO}	V_{CB} = -45 V , I_E =0		-0.1	μΑ
	BC858		V_{CB} = -25 V , I_{E} =0			
Collector cut-off current	BC856		V _{CE} = -60 V , I _B =0			
	BC857	I _{CEO}	V_{CE} = -40 V , I_{B} =0		-0.1	μΑ
	BC858		V _{CE} = -25 V , I _B =0			
Emitter cut-off current		I _{EBO}	V _{EB} = -5 V , I _C =0		-0.1	μΑ
DC current gain BC856A	A, 857A,858A			125	250	
BC856E	3, 857B,858B	h _{FE}	V_{CE} = -5V, I_{C} = -2mA	220	475	
BC8	57C,BC858C			420	800	
Collector-emitter saturation voltage		V _{CE} (sat)	I _C =-100mA, I _B = -5 mA		-0.5	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C = -100mA, I _B = -5mA		-1.1	V
Transition frequency		f⊤	V _{CE} = -5 V, I _C = -10mA f=100MHz	100		MHz
Collector capacitance		C _{ob}	V _{CB} =-10V, f=1MHz		4.5	pF

Date:2011/05



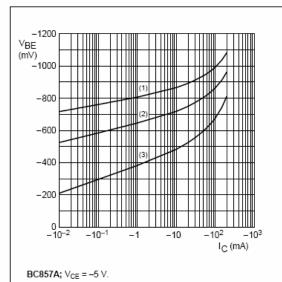
Typical Characteristics



BC857A; V_{CE} = -5 V.

- (1) T_{amb} = 150 °C.
- (2) T_{amb} = 25 °C.
- (3) T_{amb} = -55 °C.

Fig.2 DC current gain as a function of collector current; typical values.

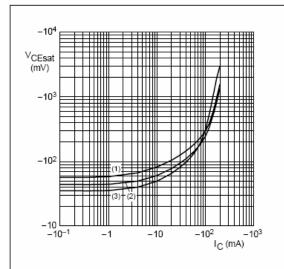


(1) $T_{amb} = -55 \,^{\circ}\text{C}$.

(2) T_{amb} = 25 °C.

(3) T_{amb} = 150 °C.

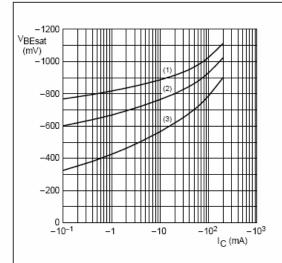
Fig.3 Base-emitter voltage as a function of collector current; typical values.



BC857A; I_C/I_B = 20.

- (1) T_{amb} = 150 °C.
- (2) T_{amb} = 25 °C.
- (3) T_{amb} = −55 °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857A; I_C/I_B = 20.

(1) T_{amb} = −55 °C.

(2) T_{amb} = 25 °C.

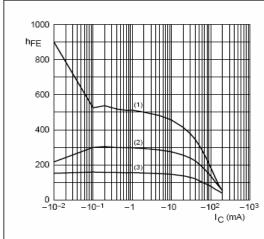
(3) T_{amb} = 150 °C.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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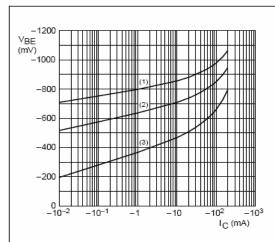
BC857B; $V_{CE} = -5 V$.

(1) T_{amb} = 150 °C.

(2) T_{amb} = 25 °C.

(3) T_{amb} = −55 °C.

Fig.6 DC current gain as a function of collector current; typical values.



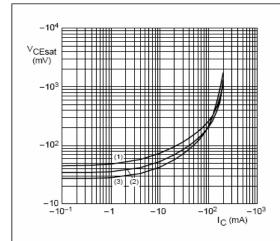
BC857B; $V_{CE} = -5 \text{ V}$.

(1) T_{amb} = −55 °C.

(2) T_{amb} = 25 °C.

(3) T_{amb} = 150 °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.

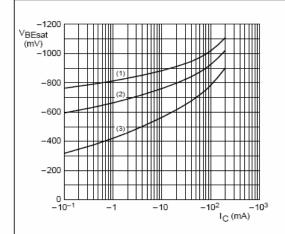


BC857B; I_C/I_B = 20.

(1) T_{amb} = 150 °C.

(2) T_{amb} = 25 °C. (3) T_{amb} = −55 °C.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



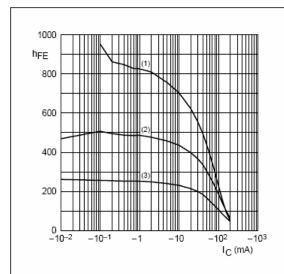
BC857B; I_C/I_B = 20.

(1) T_{amb} = −55 °C. (2) T_{amb} = 25 °C.

(3) T_{amb} = 150 °C.

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

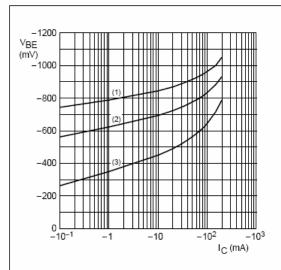




BC857C; $V_{CE} = -5 V$.

- (1) T_{amb} = 150 °C.
- (2) T_{amb} = 25 °C.
- (3) T_{amb} = -55 °C.

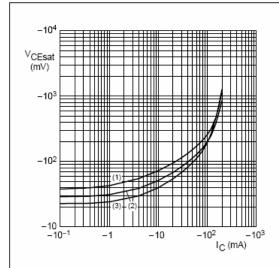
Fig.10 DC current gain as a function of collector current; typical values.



BC857C; V_{CE} = -5 V.

- (1) $T_{amb} = -55 \,^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) T_{amb} = 150 °C

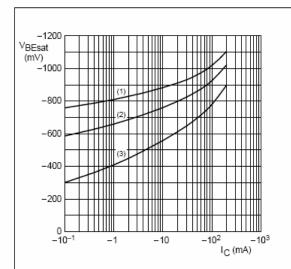
Fig.11 Base-emitter voltage as a function of collector current; typical values.



BC857C; I_C/I_B = 20.

- (1) T_{amb} = 150 °C.
- (2) T_{amb} = 25 °C.
- (3) T_{amb} = −55 °C.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857C; I_C/I_B = 20.

- (1) T_{amb} = −55 °C.
- (2) T_{amb} = 25 °C.
- (3) T_{amb} = 150 °C.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

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